

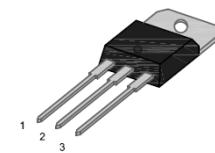
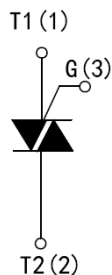
NOTE:
IMAGE SERVES AS A VISUAL
REPRESENTATION OF THE
PRODUCT ONLY.

ABSTRACT

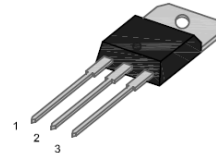
The JST20A/20B are high voltage TRIACs with high current density, SIPOS, and are glass passivated. These components are suitable for general purpose AC switching and can be used as an ON/OFF function in applications such as static relays, heating regulation, and so on. This design is specifically recommended for use on inductive loads.

FEATURES

- 2500V RMS isolation voltage from all three terminals to external heatsink
- $I_{T(RMS)} = 20A$
- $V_{DRM}/V_{RRM} = 1200V$
- $V_{TM} = 1.65V$



JST20B(TO-220B:non-Insulated)



JST20A(TO-220A:insulated)
UL file:E252906

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		Tstg	-40 to +150	°C
Operating junction temperature range		Tj	-40 to +125	°C
Repetitive Peak Off-state Voltage	Tj=25°C	VDRM	1200	V
Repetitive Peak Reverse Voltage	Tj=25°C	VRRM	1200	
Non repetitive Surge Peak Off-state Voltage	tp=10ms, Tj=25°C	VDSM	1300	V
Non repetitive Peak Reverse Voltage		VRSM	1300	
RMS on-state current (full sine wave)	JST20B Tc=88°C	IT(RMS)	20	A
	JST20A Tc=67°C			
Non repetitive surge peak on-state current (full cycle, Tj=25°C)	f=60Hz、t=16.7ms	ITSM	210	A
	f=50Hz、t=20ms		200	
I²t Value for fusing	tp=10ms	I²t	200	A²s
Critical rate of rise of on-state current IG=2×IGT, tr≤100 ns, f=120Hz, Tj=125°C		dI/dt	100	A/μs
Peak gate current (tp=20us, Tj=125°C)		IGM	4	A
Peak Gate Power Dissipation (tp=20us, Tj=125°C)		PGM	10	W
Average gate power dissipation (Tj=125°C)		PG(AV)	1	W



ELECTRICAL CHARACTERISTICS

Symbol	Test Condition	Quadrant		Limit	Unit
				BW	
IGT	VD=12V RL=33Ω	I-II-III	MAX.	50	mA
VGT		I-II-III	MAX.	1.5	V
VGD	VD=VDRM RL=3.3KΩ Tj=125°C	I-II-III	MIN.	0.2	V
IL	IG=1.2IGT	I-III	MAX.	90	mA
		II	MAX.	120	mA
IH	IT=100mA		MAX.	75	mA
dV/dt	VD=67%VDRM gate open Tj=125°C		MIN.	500	V/μs
(dV/dt)c	(dI/dt)c=8.8A/ms Tj=125°C		MIN.	12.5	V/μs

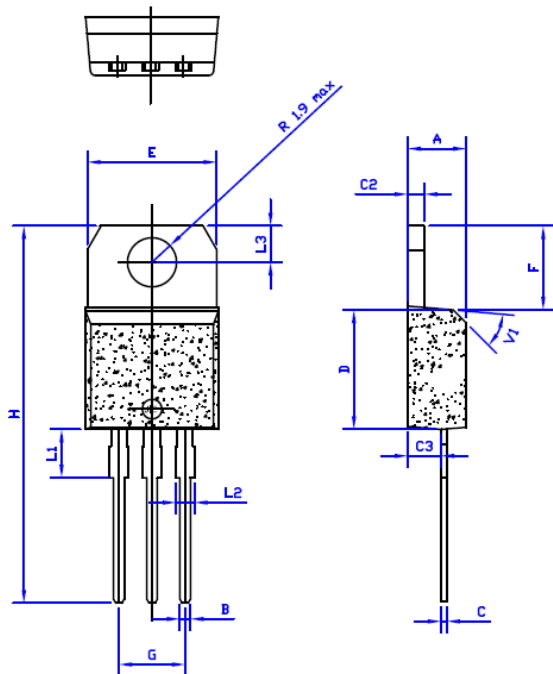
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
VTM	ITM=28A, tp=380μs	Tj=25°C	1.65	V
IDRM	VD=VDRM VR=VRRM	Tj=25°C	5	μA
IRRM		Tj=125°C	2.5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth(J -C)	Junction to Case(AC)	JST20B	1.35	°C/W
		JST20A	2.15	

DIMENSIONAL INFORMATION



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		1.181
B	0.61		0.88	0.024		0.034
C	0.46		0.70	0.018		0.027
C2	1.23		1.32	0.048		0.051
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.338		0.382
E	9.8		10.4	0.386		0.409
F	6.2		6.6	0.244		0.259
G	4.8		5.4	0.189		0.213
H	28.0		29.8	11.0		11.7
L1		3.75			0.147	
L2	1.14		1.7	0.044		0.066
L3	2.65		2.95	0.104		0.116
V1		40°			40°	

FIG.1: Maximum power dissipation versus RMS on-state current(full cycle)

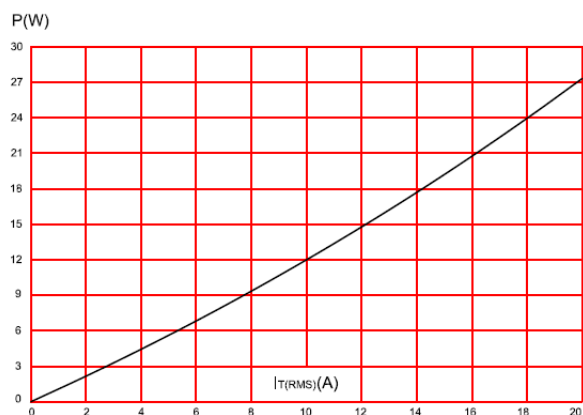


FIG.2: RMS on-state current versus case temperature(full cycle)

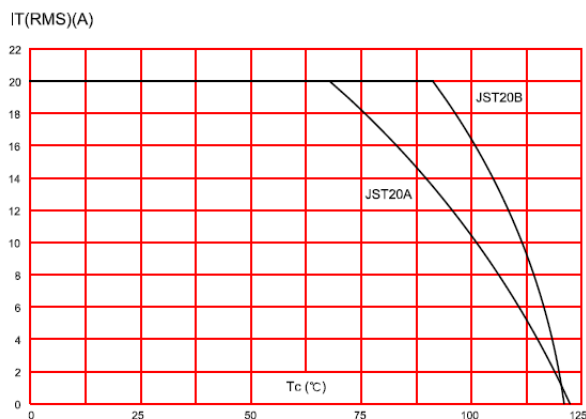


FIG.3: On-state characteristics (maximum values).

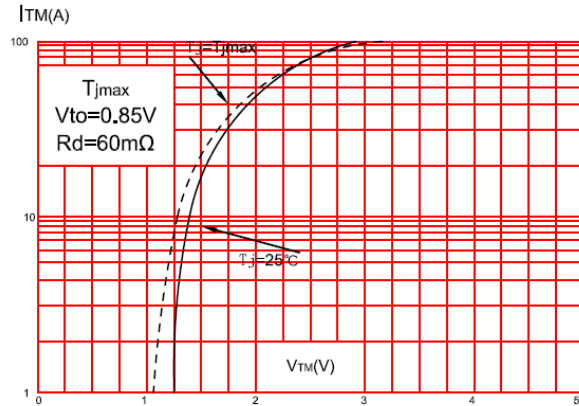


FIG.4: Surge peak on-state current versus number of cycles.

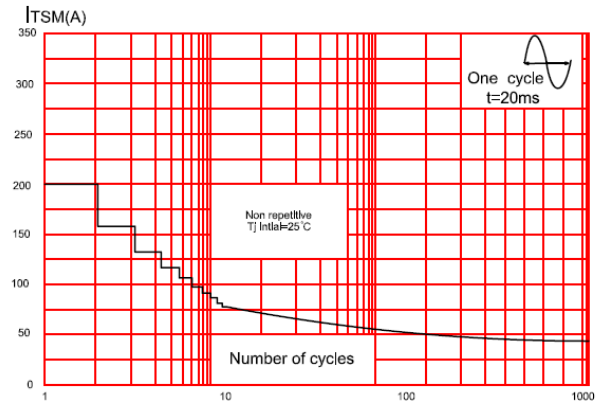


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t .

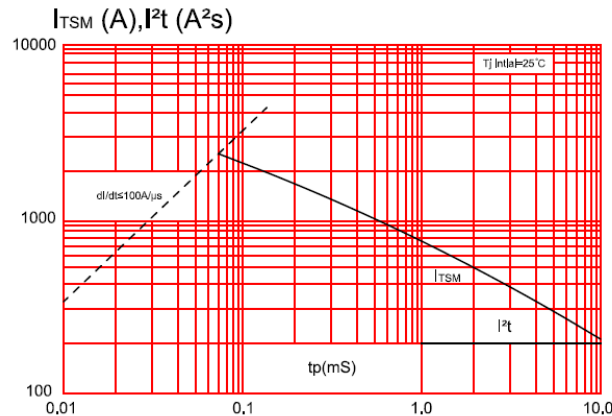


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)

